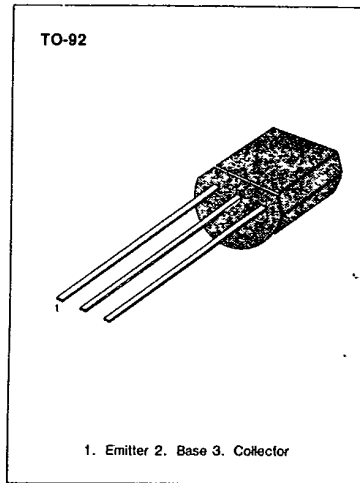


**KSC839****NPN EPITAXIAL SILICON TRANSISTOR**

T-31-17

**FM/AM RADIO RF AMP, CONV, OSC, IF AMP**• Current-Gain-Bandwidth Product  $f_T = 200\text{MHz}$ **ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	35	V
Collector-Emitter Voltage	$V_{CE0}$	30	V
Emitter-Base Voltage	$V_{EB0}$	4	V
Collector Current	$I_C$	100	mA
Collector Dissipation	$P_C$	250	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 - 150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CB0}$	$I_C = 100\mu\text{A}, I_E = 0$	35			V
Collector-Emitter Breakdown Voltage	$BV_{CE0}$	$I_C = 5\text{mA}, I_B = 0$	30			V
Emitter-Base Breakdown Voltage	$BV_{EB0}$	$I_E = 10\mu\text{A}, I_C = 0$	4			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 30\text{V}, I_E = 0$			0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 4\text{V}, I_C = 0$			0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 12\text{V}, I_C = 2\text{mA}$	40		400	
Base-Emitter On Voltage	$V_{BE(ON)}$	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	0.65	0.70	0.75	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$		0.1	0.4	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	80	200		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0$ $f = 1\text{MHz}$		2.0	3.5	pF

 **$h_{FE}$  CLASSIFICATION**

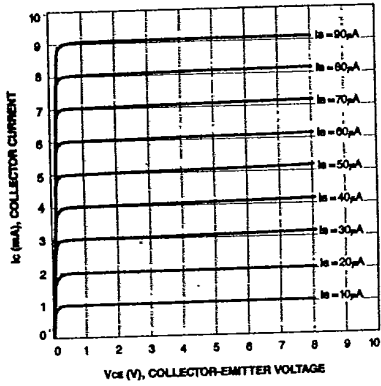
Classification	R	O	Y	G
$h_{FE}$	40-80	70-140	120-240	200-400

KSC839

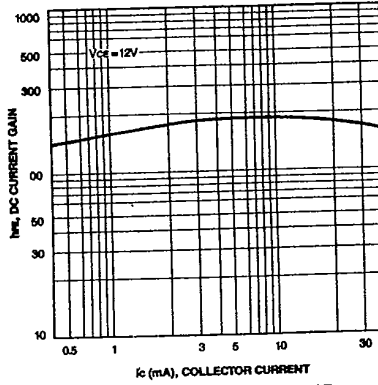
NPN EPITAXIAL SILICON TRANSISTOR

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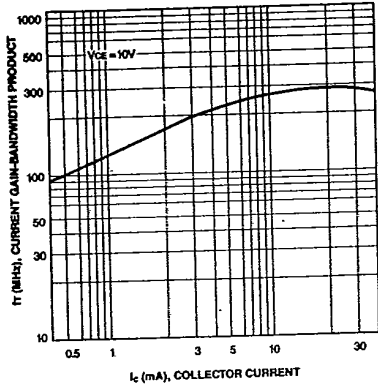
STATIC CHARACTERISTIC



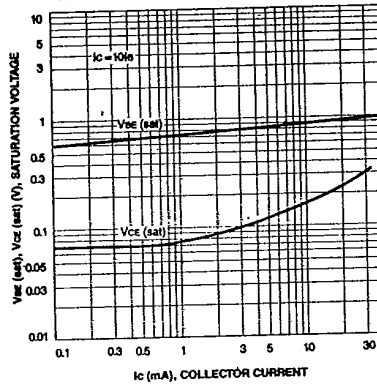
DC CURRENT GAIN



CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE  
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE

